AMENDMENTS TO THE CLAIMS:

Claims 1-9 (withdrawn)

Claim 10 (original): A method of producing a ceramic thermistor chip, said method comprising the steps of:

stacking a specified number of thermistor ceramic green sheets;

cutting and baking the stacked ceramic green sheets to obtain a ceramic thermistor element, said ceramic thermistor element having outer surfaces including two end parts away from each other;

forming a high-resistance layer entirely covering said outer surfaces of said ceramic thermistor element except said end parts;

thereafter subjecting said ceramic thermistor element to an electrolytic plating process to thereby form electrolytically plated layers on said end parts whereby said outer surfaces of said ceramic thermistor element are entirely covered by said high-resistance layer except where said electrolytically plated layers are formed.

Claim 11 (original): The method of claim 10 wherein said high-resistance layer comprises an electrically insulating organic material.

Claim 12 (original): The method of claim 11 wherein said high-resistance layer comprises an acrylate resin.

Claim 13 (original): A method of producing a ceramic thermistor chip, said method comprising the steps of:

stacking a specified number of thermistor ceramic green sheets;

cutting the stacked ceramic green sheets to obtain a ceramic thermistor element, said ceramic thermistor element having outer surfaces including two end parts away from each other;

applying a ceramic material, having a higher specified resistance than said thermistor ceramic green sheets, entirely over said outer surfaces of said ceramic thermistor element except said end parts;

thereafter baking said ceramic thermistor element with said ceramic material applied thereon; and

thereafter subjecting said baked ceramic thermistor element to an electrolytic plating process to thereby form electrolytically plated layers on said end parts whereby said outer

surfaces of said ceramic thermistor element are entirely covered by said high-resistance layer except where said electrolytically plated layers are formed.

Claim 14 (original): The method of claim 13 wherein said ceramic layer and said thermistor element both have a same principal component by 10% or more.

Claim 15 (original): The method of claim 13 wherein said ceramic thermistor element has a specific resistance lower than 200Ω·cm.

Claim 16 (original): The method of claim 13 wherein said ceramic layer comprises one or more oxides containing two or more metals selected from the group consisting of Mn, Ni, Co, Fe, Cu and Al and also at least one metal selected from the group consisting of Zn, Al, W, Zr, Sb, Y, Sm, Ti and Fe.

Claim 17 (original): The method of claim 13 wherein said ceramic layer comprises one or more oxides containing two or more metals selected from the group consisting of Mn, Ni, Co, Fe, Cu and Al and also at least one metal selected from the group consisting of Zn, Al, W, Zr, Sb, Y, Sm, Ti and Fe.

Claim 18 (original): The method of claim 14 wherein said principal component consists of one or more oxides containing two or more metals selected from the group consisting of Mn, Ni, Co, Fe, Cu and Al and also at least one metal selected from the group consisting of Zn, Al, W, Zr, Sb, Y, Sm, Ti and Fe.